

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	4274	(gate near10 (oxide dielectric insulat\$3) near10 amorph\$8)	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/09 12:26
L3	1116	(implant\$3 dop\$4) near10 (gate near10 (oxide dielectric insulat\$3) near10 amorph\$8)	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/09 14:17
L4	1092	3 and (etch\$3 pattern\$4)	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/09 14:12
L5	506	4 and (gate near5 mask)	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/09 14:12
L6	1414	(implant\$3 dop\$4) and (gate near10 (oxide dielectric insulat\$3) and amorph\$8)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:12
L7	780	6 and (etch\$3 pattern\$4)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:12
L8	118	7 and (gate near5 mask)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:13
L9	2858	(amorph\$8 near5 (gate near5 (oxide dielectric insulat\$3)))	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/09 14:18
L10	1525	9 and ((etch\$3 pattern\$4) near5 (gate near5 (oxide dielectric insulat\$3)))	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/09 14:19
L11	1249	10 and mask	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/09 14:19
L12	1249	11 and gate	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/09 14:21